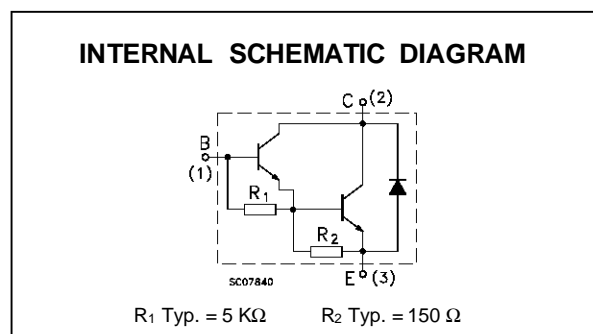
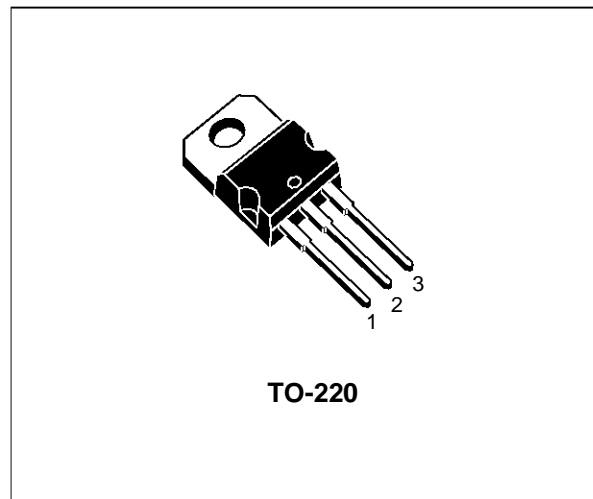


**COMPLEMENTARY SILICON POWER
DARLINGTON TRANSISTORS**

■ SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The TIP100, and TIP102 are silicon epitaxial-base NPN transistors in monolithic Darlington configuration mounted in TO-220 plastic package intended for use in power linear and switching applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit	
		NPN	TIP100		TIP102
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)		5		V
I _C	Collector Current		8		A
I _{CM}	Collector Peak Current		15		A
I _B	Base Current		1		A
P _{tot}	Total Dissipation at T _{case} ≤ 25 °C T _{amb} ≤ 25 °C		80		W
			2		W
T _{stg}	Storage Temperature		-65 to 150		°C
T _j	Max. Operating Junction Temperature		150		°C

* For PNP types voltage and current values are negative.

TIP100/TIP102

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.56	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

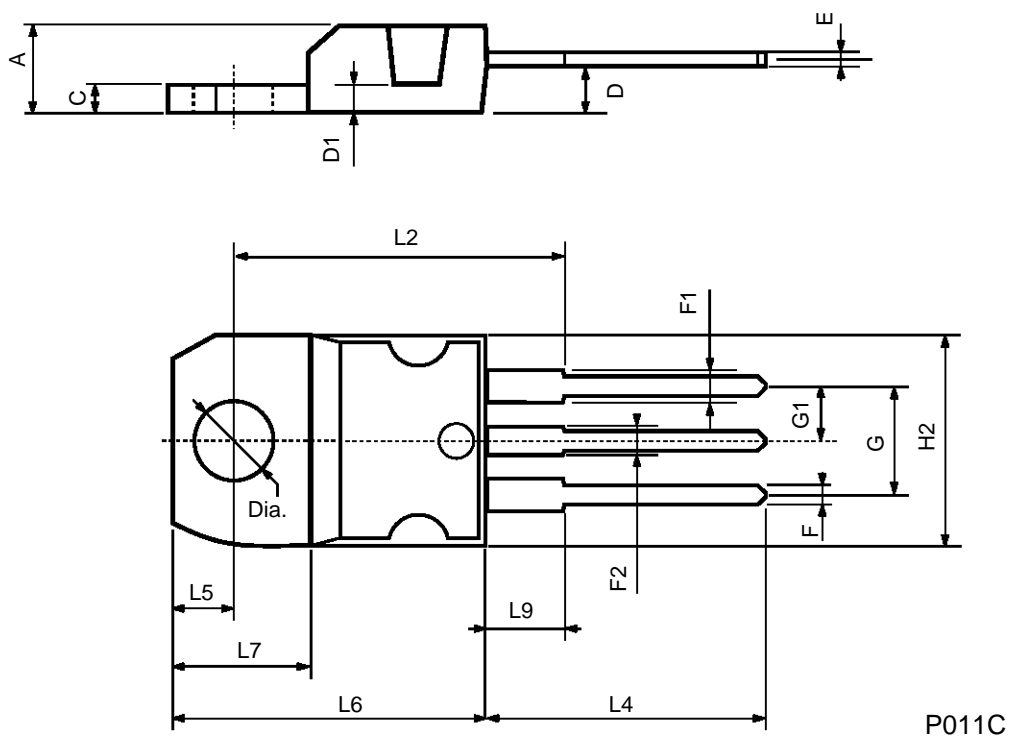
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	for TIP100 V _{CE} = 30 V for TIP102 V _{CE} = 50 V			50 50	μA μA
I _{CBO}	Collector Cut-off Current (I _E = 0)	for TIP100 V _{CE} = 60 V for TIP102 V _{CE} = 100 V			50 50	μA μA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			8	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP100 for TIP102	60 100			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 3 A I _B = 6 mA I _C = 8 A I _B = 80 mA			2 2.5	V V
V _{BE} *	Base-Emitter Voltage	I _C = 8 A V _{CE} = 4 V			2.8	V
h _{FE} *	DC Current Gain	I _C = 3 A V _{CE} = 4 V I _C = 8 A V _{CE} = 4 V	1000 500		20000	
V _F *	Forward Voltage of Commutation Diode (I _B = 0)	I _F = - I _C = 10 A			2.8	V

* For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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